

FIG. 1

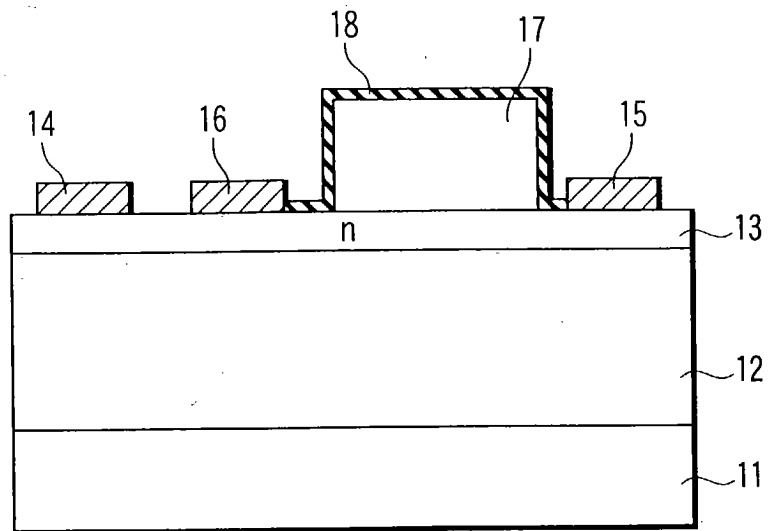


FIG. 2

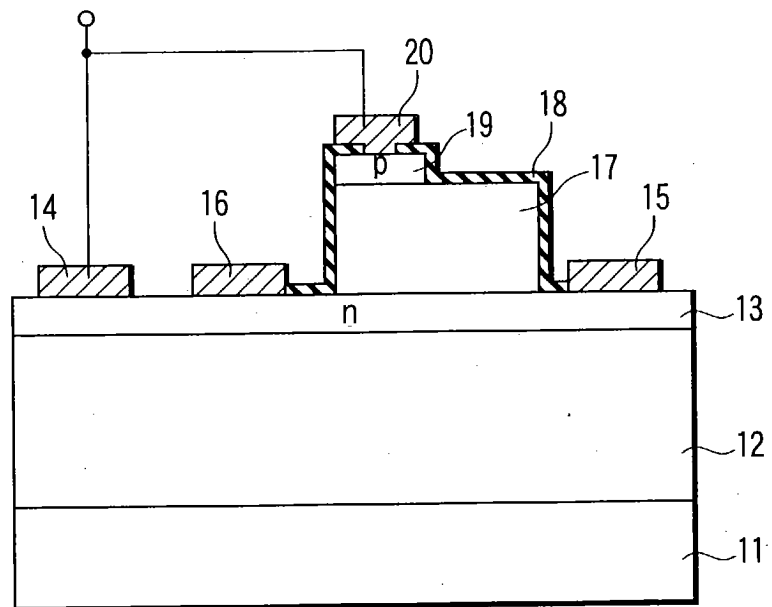
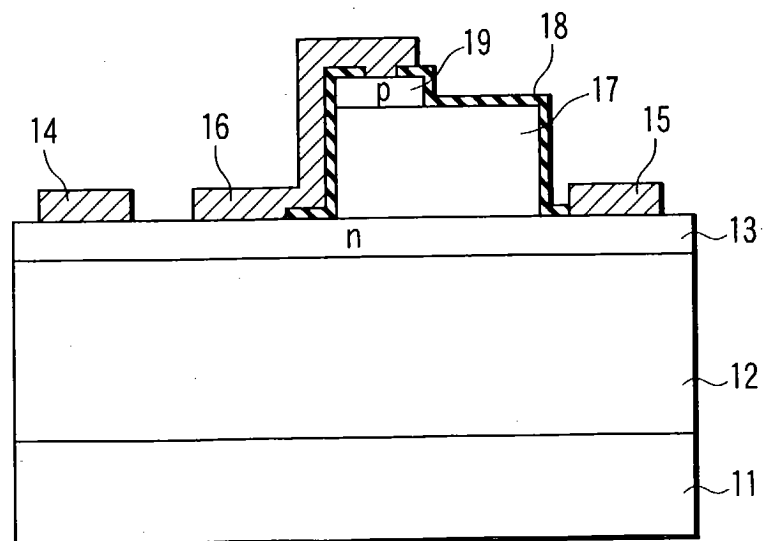


FIG. 3



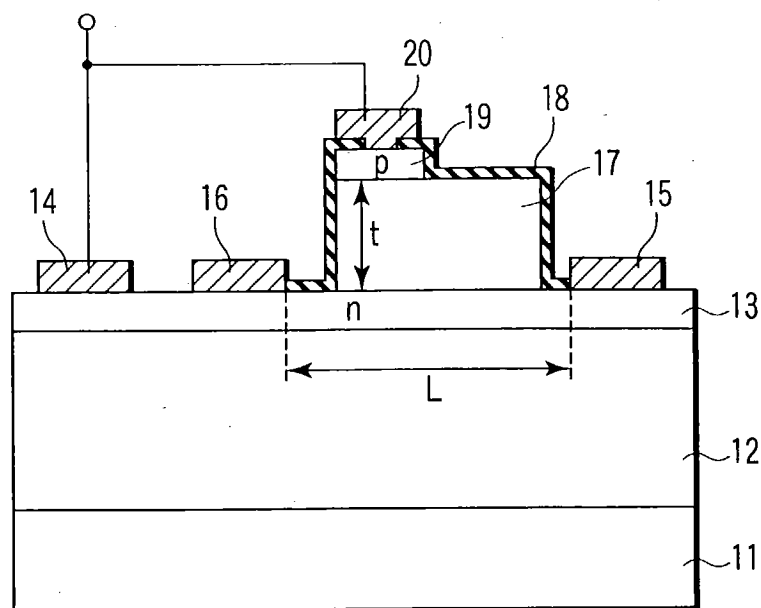


FIG. 4

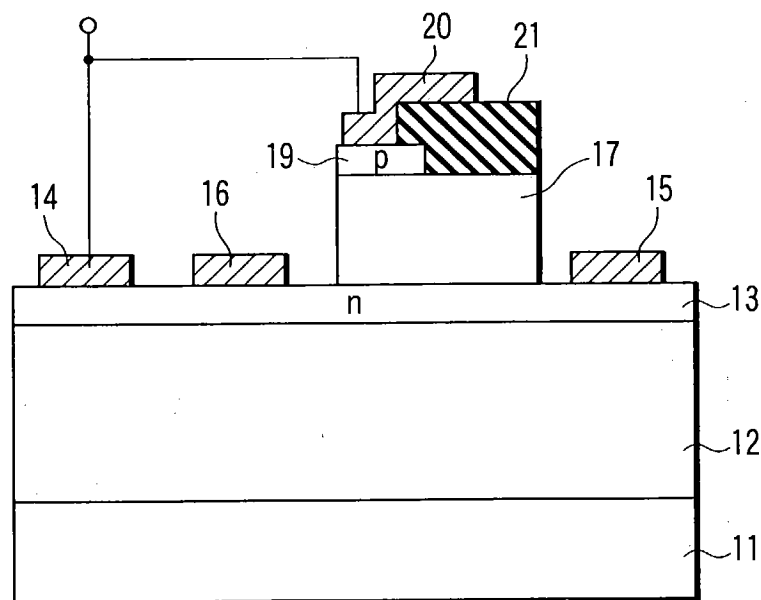


FIG. 5

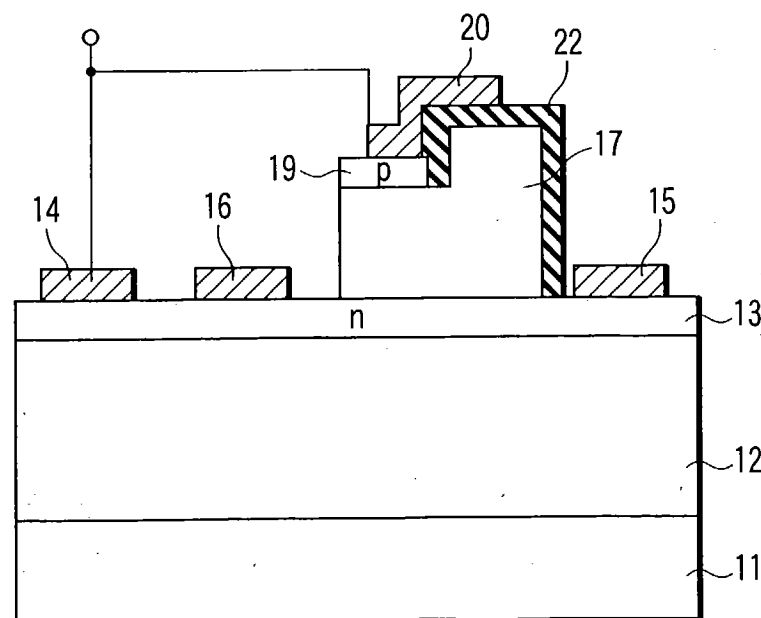


FIG. 6

FIG. 7

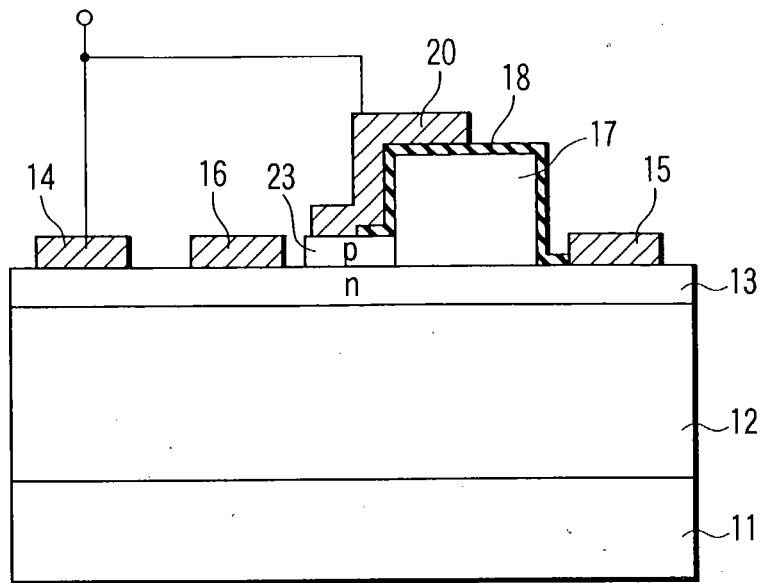


FIG. 8

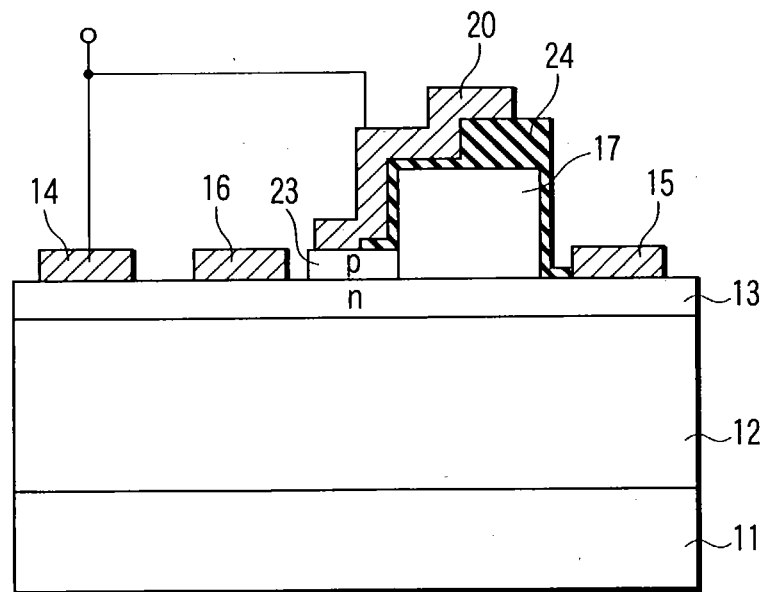


FIG. 9

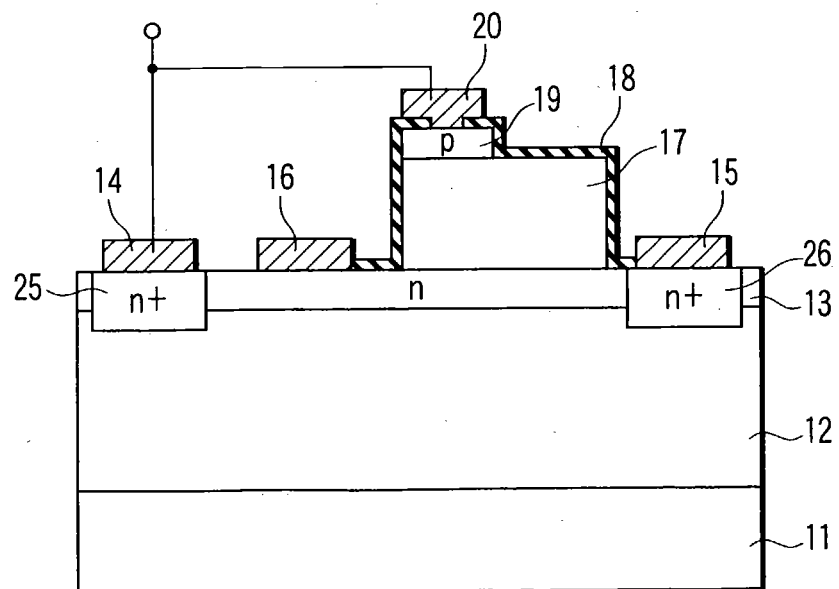


FIG. 12

FIG. 13

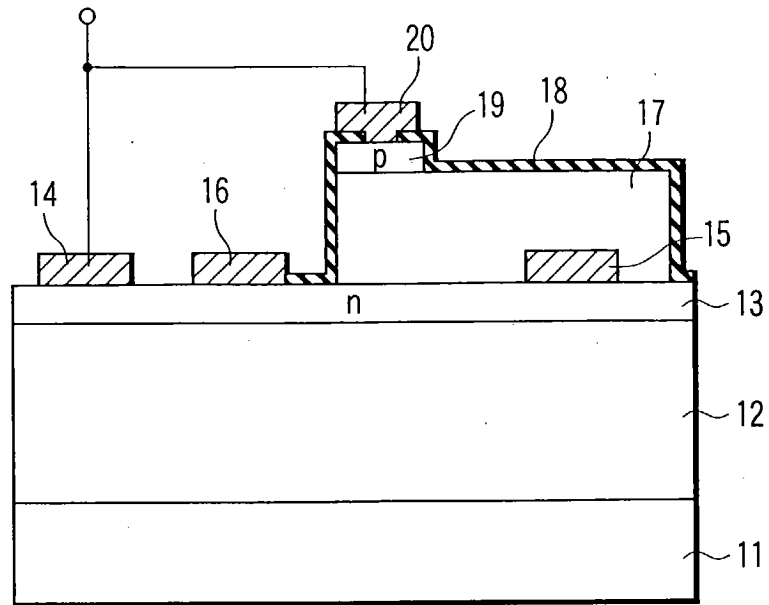


FIG. 14

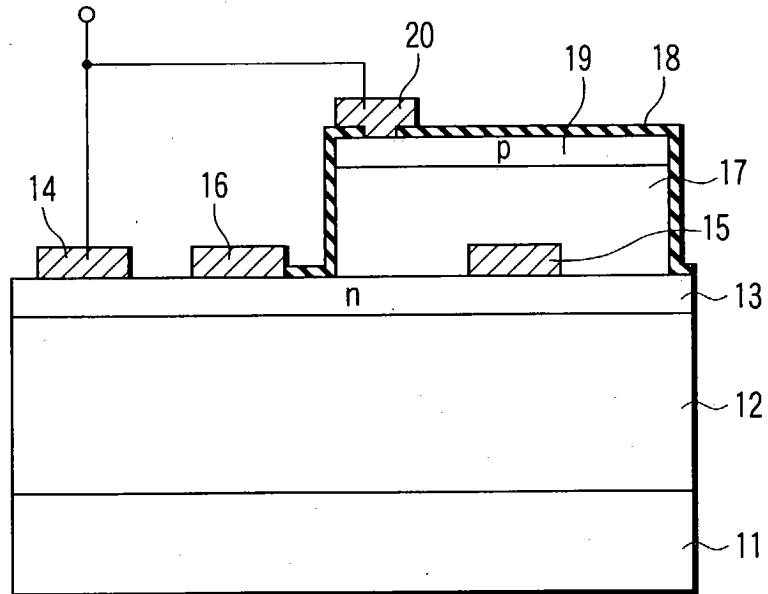


FIG. 15

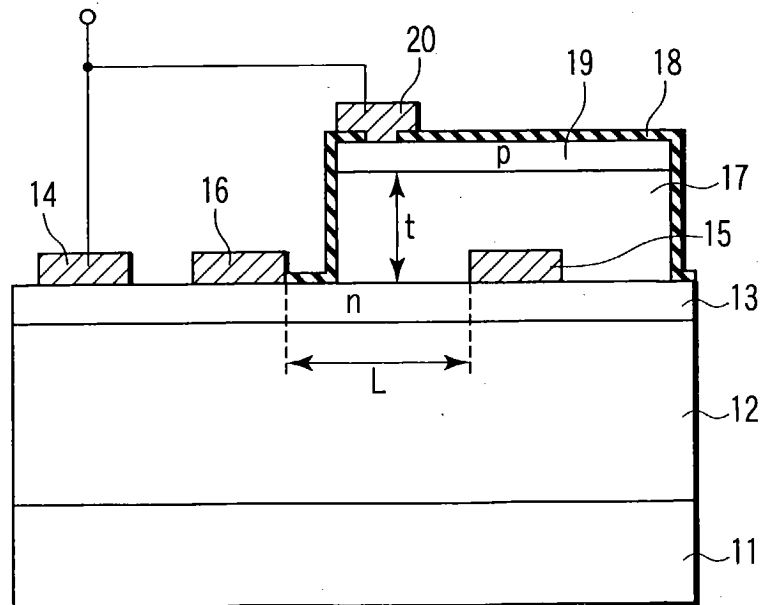


FIG. 16

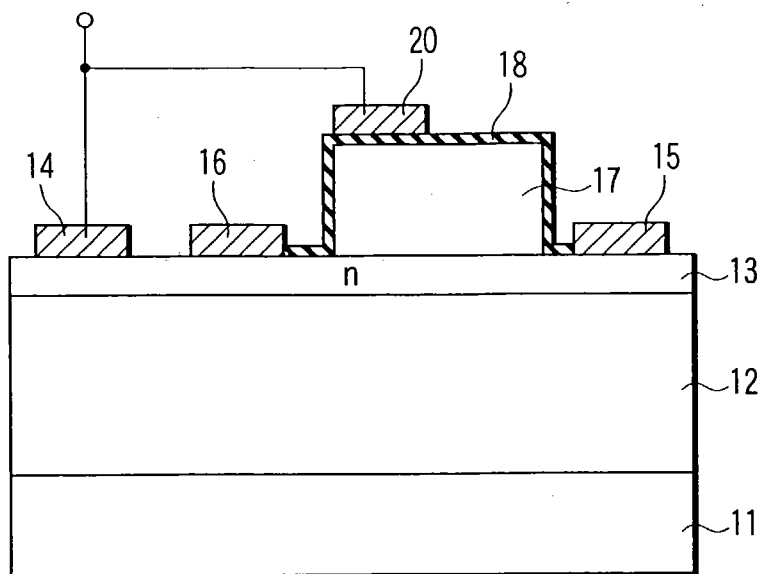


FIG. 17

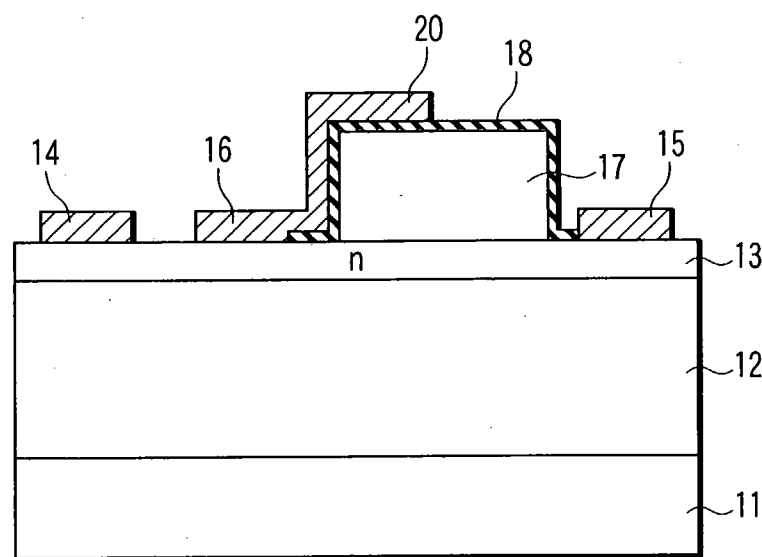
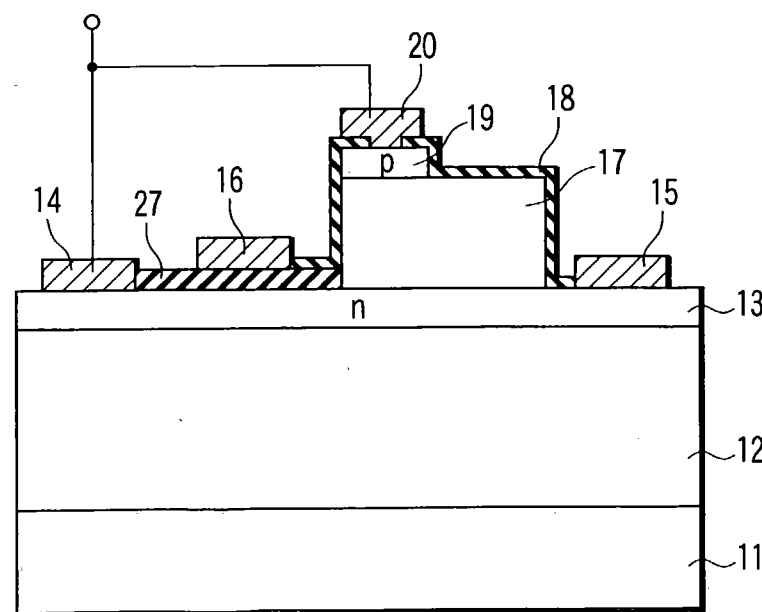


FIG. 18



A cross-sectional diagram of a GaN-based device structure. The structure consists of several layers: a p-GaN layer (19) at the bottom, followed by a GaN layer (12), an n-AlGaN layer (31), and an undoped AlGaN layer (32) at the top. The diagram shows a cross-section with a central region where the layers are stacked, and side regions where the layers are more uniform. Labels A and A' indicate specific points or regions on the structure.

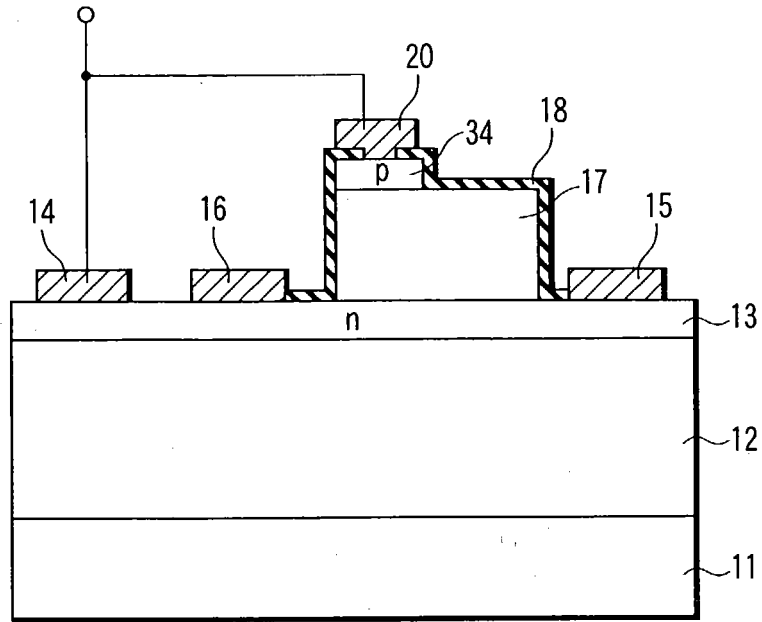


FIG. 21

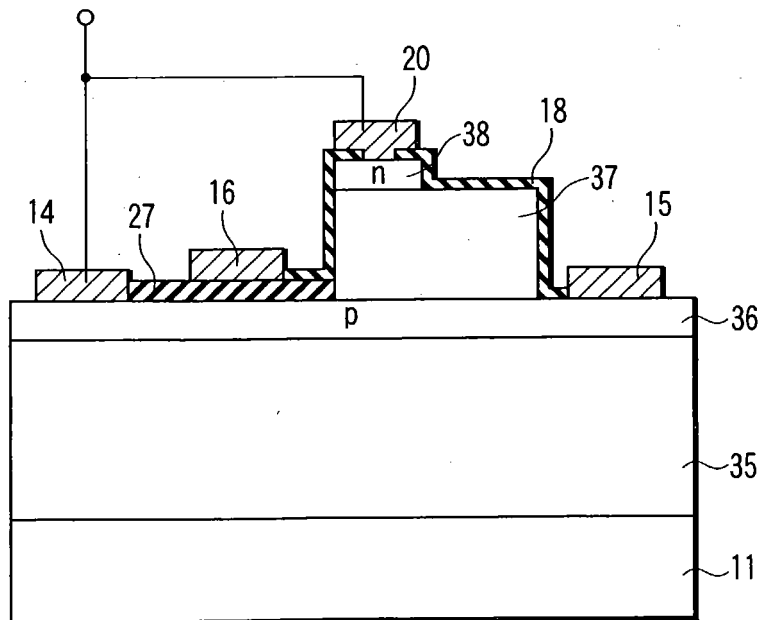


FIG. 22



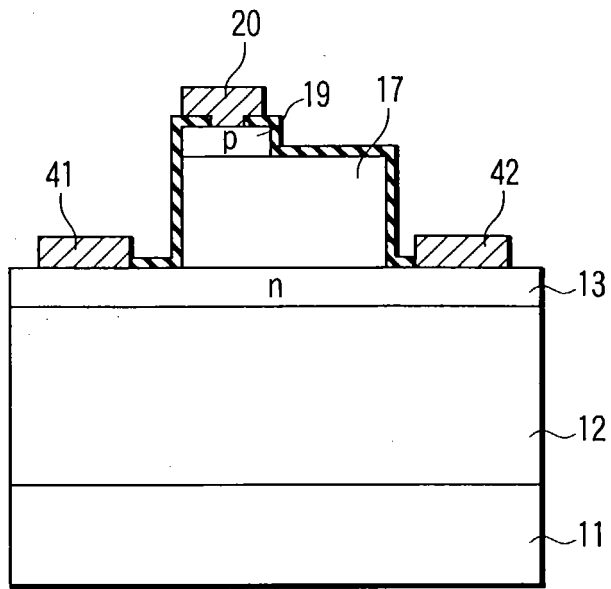


FIG. 23

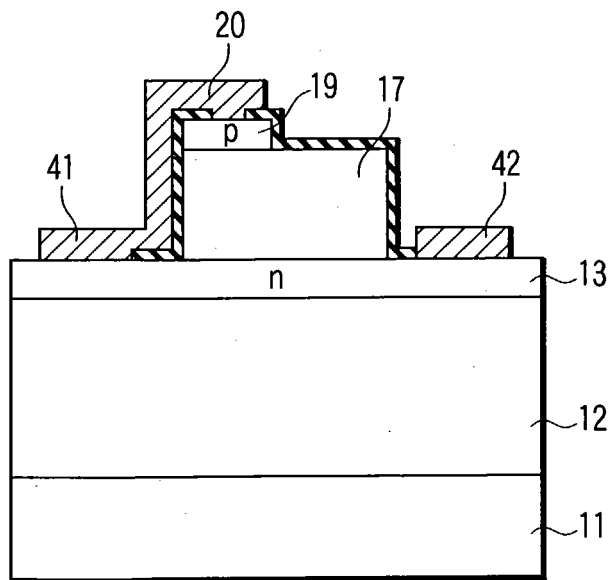


FIG. 24